

Thierry Chassagne

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

97
papers

1,253
citations

20
h-index

31
g-index

101
ext. papers

1,318
ext. citations

1.6
avg, IF

3.66
L-index

#	Paper	IF	Citations
97	Structural Quality, Polishing and Thermal Stability of 3C-SiC/Si Templates. <i>Materials Science Forum</i> , 2018 , 924, 306-309	0.4	9
96	Influence of Aluminum Incorporation on Mechanical Properties of 3C-SiC Epilayers. <i>Materials Science Forum</i> , 2018 , 924, 318-321	0.4	2
95	High temperature annealing and CVD growth of few-layer graphene on bulk AlN and AlN templates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017 , 214, 1600436	1.6	8
94	Electrical transport properties of p-type 4H-SiC. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017 , 214, 1600679	1.6	17
93	Influence of Growth Temperature on Site Competition Effects during Chemical Vapor Deposition of 4H-SiC Layers. <i>Materials Science Forum</i> , 2017 , 897, 79-82	0.4	
92	CVD Growth of Graphene on SiC (0001): Influence of Substrate Offcut. <i>Materials Science Forum</i> , 2017 , 897, 731-734	0.4	3
91	Comparative Study of p-Type 4H-SiC Grown on n-Type and Semi Insulating 4H-SiC Substrates. <i>Materials Science Forum</i> , 2017 , 897, 275-278	0.4	1
90	Processing and Characterization of MOS Capacitors Fabricated on 2°-Off Axis 4H-SiC Epilayers. <i>Materials Science Forum</i> , 2016 , 858, 663-666	0.4	
89	Novel 3C-SiC Microstructure for MEMS Applications. <i>Materials Science Forum</i> , 2016 , 858, 723-728	0.4	1
88	Electrical properties of SiO ₂ /SiC interfaces on 2°-off axis 4H-SiC epilayers. <i>Applied Surface Science</i> , 2016 , 364, 892-895	6.7	5
87	Realization of minimum number of rotational domains in heteroepitaxial Si(110) on 3C-SiC(001). <i>Applied Physics Letters</i> , 2016 , 108, 011608	3.4	4
86	Effect of germanium doping on electrical properties of n-type 4H-SiC homoepitaxial layers grown by chemical vapor deposition. <i>Journal of Applied Physics</i> , 2016 , 120, 205701	2.5	5
85	p-Type Doping of 4H- and 3C-SiC Epitaxial Layers with Aluminum. <i>Materials Science Forum</i> , 2016 , 858, 137-142	0.4	13
84	Electrical Transport Properties of Highly Aluminum Doped p-Type 4H-SiC. <i>Materials Science Forum</i> , 2016 , 858, 249-252	0.4	3
83	Structural Investigation of Si Quantum Dots Grown by CVD on AlN/Si(111) and 3C-SiC/Si(100) Epilayers. <i>Materials Science Forum</i> , 2015 , 821-823, 1003-1006	0.4	
82	Quantum Hall resistance standards from graphene grown by chemical vapour deposition on silicon carbide. <i>Nature Communications</i> , 2015 , 6, 6806	17.4	58
81	Influence of Site Competition Effects on Dopant Incorporation during Chemical Vapor Deposition of 4H-SiC Epitaxial Layers. <i>Materials Science Forum</i> , 2015 , 821-823, 149-152	0.4	1

80	Silicon Growth on 3C-SiC(001)/Si(001): Pressure Influence and Thermal Effect. <i>Materials Science Forum</i> , 2015 , 821-823, 978-981	0.4	5
79	Graphene growth on AlN templates on silicon using propane-hydrogen chemical vapor deposition. <i>Applied Physics Letters</i> , 2014 , 104, 071912	3.4	15
78	Electrothermally driven high-frequency piezoresistive SiC cantilevers for dynamic atomic force microscopy. <i>Journal of Applied Physics</i> , 2014 , 116, 054304	2.5	10
77	Structural trends in Si dots formation on SiC surfaces using CVD environment. <i>Journal of Crystal Growth</i> , 2014 , 404, 157-163	1.6	3
76	Influence of 3C-SiC/Si (111) template properties on the strain relaxation in thick GaN films. <i>Journal of Crystal Growth</i> , 2014 , 398, 23-32	1.6	12
75	Probing at Nanoscale Underneath the Gate Oxides in 4H-SiC MOS-Based Devices Annealed in N ₂ O and POCl ₃ . <i>Materials Science Forum</i> , 2014 , 806, 143-147	0.4	
74	Investigation of Aluminum Incorporation in 4H-SiC Epitaxial Layers. <i>Materials Science Forum</i> , 2014 , 806, 45-50	0.4	2
73	3C-SiC: New Interest for MEMS Devices. <i>Materials Science Forum</i> , 2014 , 806, 3-9	0.4	3
72	Original 3C-SiC micro-structure on a 3C-SiC pseudo-substrate. <i>Microelectronic Engineering</i> , 2013 , 105, 65-67	2.5	12
71	Effects of pressure, temperature, and hydrogen during graphene growth on SiC(0001) using propane-hydrogen chemical vapor deposition. <i>Journal of Applied Physics</i> , 2013 , 113, 203501	2.5	29
70	X-Ray Diffraction and Raman Spectroscopy Study of Strain in Graphene Films Grown on 6H-SiC(0001) Using Propane-Hydrogen-Argon CVD. <i>Materials Science Forum</i> , 2013 , 740-742, 117-120	0.4	10
69	A new approach for AFM cantilever elaboration with 3C-SiC. <i>Materials Letters</i> , 2012 , 77, 54-56	3.3	13
68	Growth mode and electric properties of graphene and graphitic phase grown by argon/propane assisted CVD on 3C-SiC/Si and 6H-SiC. <i>Journal of Crystal Growth</i> , 2012 , 349, 27-35	1.6	26
67	Experimental observation and analytical model of the stress gradient inversion in 3C-SiC layers on silicon. <i>Journal of Applied Physics</i> , 2012 , 111, 053507	2.5	18
66	Graphene growth using propane-hydrogen CVD on 6H-SiC(0001): temperature dependent interface and strain. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 175-178		11
65	Structural and Electrical Properties of Graphene Films Grown by Propane/Hydrogen CVD on 6H-SiC(0001). <i>Materials Science Forum</i> , 2012 , 717-720, 625-628	0.4	3
64	Ti Thickness Influence for Ti/Ni Ohmic Contacts on N-Type 3C-SiC. <i>Materials Science Forum</i> , 2012 , 711, 179-183	0.4	4
63	Dose Influence on Physical and Electrical Properties of Nitrogen Implantation in 3C-SiC on Si. <i>Materials Science Forum</i> , 2012 , 711, 154-158	0.4	4

62	Detailed Experimental Study of Mean and Gradient Stresses in Thin 3C-SiC Films Performed Using Micromachined Cantilevers. <i>Materials Science Forum</i> , 2012 , 711, 84-88	0.4	1
61	Graphene/SiC Interface Control Using Propane-Hydrogen CVD on 6H-SiC(0001) and 3C-SiC(111)/Si(111). <i>Materials Science Forum</i> , 2012 , 711, 253-257	0.4	3
60	Elaboration of Monocrystalline Si Thin Film on 3C-SiC(100)/Si Epilayers by Low Pressure Chemical Vapor Deposition. <i>Materials Science Forum</i> , 2012 , 711, 61-65	0.4	7
59	CVD Growth of Graphene on 2BC-SiC/Si Templates: Influence of Substrate Orientation and Wafer Homogeneity. <i>Materials Science Forum</i> , 2012 , 717-720, 621-624	0.4	1
58	Structural and electrical characterizations of n-type implanted layers and ohmic contacts on 3C-SiC. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2011 , 269, 2020-2025	1.2	12
57	Electrical Characterization of Nitrogen Implanted 3C-SiC by SSRM and C ₁ S ₁ LM Measurements. <i>Materials Science Forum</i> , 2011 , 679-680, 193-196	0.4	6
56	Analytical Model of Stress Relaxation in 3C SiC Layers on Silicon. <i>Materials Science Forum</i> , 2011 , 679-680, 79-82	0.4	3
55	Epitaxial Graphene Elaborated on 3C-SiC(111)/Si Epilayers. <i>Materials Science Forum</i> , 2010 , 645-648, 585-588	0.4	4
54	Thermally Induced Surface Reorganization of 3C-SiC(111) Epilayers Grown on Silicon Substrates. <i>Materials Science Forum</i> , 2010 , 645-648, 155-158	0.4	2
53	Micromachining of thin 3C-SiC films for mechanical properties investigation. <i>Materials Research Society Symposia Proceedings</i> , 2010 , 1246, 1		11
52	SiC on SOI Resonators: A Route for Electrically Driven MEMS in Harsh Environment. <i>Materials Science Forum</i> , 2010 , 645-648, 845-848	0.4	1
51	Recent Advances in Surface Preparation of Silicon Carbide and other Wide Band Gap Materials. <i>Materials Science Forum</i> , 2010 , 645-648, 753-758	0.4	11
50	Evidence of electrical activity of extended defects in 3CBiC grown on Si. <i>Applied Physics Letters</i> , 2010 , 96, 142104	3.4	58
49	Direct growth of few-layer graphene on 6H-SiC and 3C-SiC/Si via propane chemical vapor deposition. <i>Applied Physics Letters</i> , 2010 , 97, 171909	3.4	63
48	High Quality Ohmic Contacts on n-type 3C-SiC Obtained by High and Low Process Temperature 2010 ,		9
47	Detailed study of the influence of surface misorientation on the density of Anti-Phase Boundaries in 3C-SiC layers grown on (001) silicon 2010 ,		6
46	Epitaxial graphene on cubic SiC(111)Si(111) substrate. <i>Applied Physics Letters</i> , 2010 , 96, 191910	3.4	93
45	TiN _x ohmic contacts on 3CBiC doped by nitrogen or phosphorus implantation. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2010 , 171, 120-126	3.1	15

44	Transmission electron microscopy investigation of microtwins and double positioning domains in (111) 3C-SiC in relation with the carbonization conditions. <i>Applied Physics Letters</i> , 2009 , 95, 081903	3.4	22
43	Comparative study of the role of the nucleation stage on the final crystalline quality of (111) and (100) silicon carbide films deposited on silicon substrates.. <i>Journal of Applied Physics</i> , 2009 , 105, 083505	2.5	54
42	8H Stacking Faults in a 4H-SiC Matrix: Simple Unit Cell or Double 3C Quantum Well?. <i>Materials Science Forum</i> , 2009 , 615-617, 339-342	0.4	2
41	Role of Substrate Misorientation in Relaxation of 3C-SiC Layers on Silicon. <i>Materials Science Forum</i> , 2009 , 615-617, 169-172	0.4	8
40	Advances in Liquid Phase Conversion of (100) and (111) Oriented Si Wafers into Self-Standing 3C-SiC. <i>Materials Science Forum</i> , 2009 , 615-617, 49-52	0.4	1
39	Combined structural and optical studies of stacking faults in 4H-SiC layers grown by chemical vapour deposition. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2009 , 206, 1924-1930	1.6	7
38	Elaboration of (111) oriented 3C _B SiC/Si layers for template application in nitride epitaxy. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2009 , 165, 9-14	3.1	25
37	Highly sensitive determination of N ⁺ doping level in 3C _B SiC and GaN epilayers by Fourier transform infrared spectroscopy. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2009 , 165, 42-46	3.1	4
36	Growth and Characterization of AlGa _N /Ga _N HEMT Structures on 3C-SiC/Si(111) Templates. <i>Materials Science Forum</i> , 2008 , 600-603, 1277-1280	0.4	1
35	Observation of Asymmetric Wafer Bending for 3C-SiC Thin Films Grown on Misoriented Silicon Substrates. <i>Materials Research Society Symposia Proceedings</i> , 2008 , 1069, 1		5
34	Strain in 3C _B SiC Heteroepitaxial Layers Grown on (100) and (111) Oriented Silicon Substrates. <i>Materials Science Forum</i> , 2008 , 600-603, 207-210	0.4	5
33	Growth of AlGa _N /Ga _N HEMTs on 3C-SiC/Si(111) Substrates. <i>Materials Research Society Symposia Proceedings</i> , 2008 , 1068, 1		
32	P Implantation Effect on Specific Contact Resistance in 3C-SiC Grown on Si. <i>Materials Research Society Symposia Proceedings</i> , 2008 , 1068, 1		2
31	Structural and Morphological Characterization of 3C-SiC Films Grown on (111), (211) and (100) Silicon Substrates. <i>Materials Science Forum</i> , 2008 , 600-603, 231-234	0.4	6
30	Realization of AlGa _N /Ga _N HEMTs on 3C-SiC/Si(111) substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008 , 5, 1983-1985		8
29	Nitrogen doping of 3C-SiC thin films grown by CVD in a resistively heated horizontal hot-wall reactor. <i>Journal of Crystal Growth</i> , 2008 , 310, 3174-3182	1.6	37
28	AlGa _N /Ga _N high electron mobility transistors grown on 3C-SiC/Si(1 1 1). <i>Journal of Crystal Growth</i> , 2008 , 310, 4417-4423	1.6	36
27	Fabrication of monocrystalline 3C _B SiC resonators for MHz frequency sensors applications. <i>Sensors and Actuators B: Chemical</i> , 2008 , 133, 276-280	8.5	22

26	Photoluminescence, cathodo-luminescence and micro-Raman spectroscopy of as-grown stacking faults in 4H-SiC. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007 , 4, 1513-1516		
25	Strain and wafer curvature of 3C-SiC films on silicon: influence of the growth conditions. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2007 , 204, 981-986	1.6	51
24	Cathodoluminescence investigation of stacking faults extension in 4H-SiC. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2007 , 204, 2222-2228	1.6	5
23	Screening the built-in electric field in 4H silicon carbide stacking faults. <i>Applied Physics Letters</i> , 2007 , 90, 111902	3.4	8
22	Low Specific Contact Resistance to 3C-SiC Grown on (100) Si Substrates. <i>Materials Science Forum</i> , 2007 , 556-557, 721-724	0.4	8
21	Electric-Field Screening Effects in the Micro-Photoluminescence Spectra of As-Grown Stacking Faults in 4H-SiC. <i>Materials Science Forum</i> , 2007 , 556-557, 351-354	0.4	
20	Trends in Dopant Incorporation for 3C-SiC Films on Silicon. <i>Materials Science Forum</i> , 2007 , 556-557, 207-210	0.4	6
19	Strain Tailoring in 3C-SiC Heteroepitaxial Layers Grown on Si(100). <i>Chemical Vapor Deposition</i> , 2006 , 12, 483-488		35
18	Stress relaxation during the growth of 3C-SiC _{Bi} thin films. <i>Applied Physics Letters</i> , 2006 , 89, 131906	3.4	38
17	Control of 3C _{Bi} C/Si wafer bending by the checker-board carbonization method. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2005 , 202, 524-530	1.6	17
16	Behaviour of the 3C _{Bi} C(100) c(2 × 2) (C-terminated) and 3 × 3 (Si-rich) surface reconstructions upon initial H ₂ /CH ₄ microwave plasma exposures. <i>Physica Status Solidi A</i> , 2005 , 202, 2234-2239		3
15	Nucleation Control in FLASIC Assisted Short Time Liquid Phase Epitaxy by Melt Modification. <i>Materials Science Forum</i> , 2005 , 483-485, 213-216	0.4	2
14	Optical Investigation of the Built-In Strain in 3C-SiC Epilayers. <i>Materials Science Forum</i> , 2004 , 457-460, 657-660	0.4	3
13	Checker-Board Carbonization for Control and Reduction of the Mean Curvature of 3C-SiC Layers Grown on Si(100) Substrates. <i>Materials Science Forum</i> , 2004 , 457-460, 265-268	0.4	5
12	Investigation of 2 Inch SiC Layers Grown in a Resistively-Heated LP-CVD Reactor with Horizontal "Hot-Walls". <i>Materials Science Forum</i> , 2004 , 457-460, 273-276	0.4	29
11	Study of surface defects on 3C _{Bi} C films grown on Si(111) by CVD. <i>Journal of Crystal Growth</i> , 2003 , 253, 95-101	1.6	25
10	Interfacial strain in 3C-SiC/Si(100) pseudo-substrates for cubic nitride epitaxy. <i>Physica Status Solidi A</i> , 2003 , 195, 18-25		17
9	Correlation between epitaxial growth conditions of 3C _{Bi} C thin films on Si and mechanical behavior of 3C _{Bi} C self-suspended membranes. <i>Sensors and Actuators A: Physical</i> , 2002 , 99, 31-34	3.9	12

8	A comprehensive study of SiC growth processes in a VPE reactor. <i>Thin Solid Films</i> , 2002 , 402, 83-89	2.2	43
7	Structural properties of undoped and doped cubic GaN grown on SiC(001). <i>Journal of Applied Physics</i> , 2002 , 91, 4983-4987	2.5	35
6	Improved SiCOI Structures Elaborated by Heteroepitaxy of 3C-SiC on SOI. <i>Materials Science Forum</i> , 2002 , 389-393, 343-346	0.4	8
5	p and n type doping of cubic GaN on SiC (001). <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2001 , 82, 59-61	3.1	14
4	How to Grow Unstrained 3C-SiC Heteroepitaxial Layers on Si (100) Substrates. <i>Materials Science Forum</i> , 2001 , 353-356, 155-158	0.4	21
3	Control of Stress with Growth Conditions and Mechanical Parameters Determination of 3C-SiC Heteroepitaxial Thin Films. <i>Materials Research Society Symposia Proceedings</i> , 2000 , 657, 5201		1
2	Characterization of 3C-SiC/SOI Deposited with HMDS. <i>Materials Science Forum</i> , 2000 , 338-342, 599-602	0.4	6
1	3C-SiC Pseudosubstrates for the Growth of Cubic GaN. <i>Materials Science Forum</i> , 2000 , 338-342, 1467-1470	0.4	4